

DSF8045SK

Fast Recovery Diode

Q_r t_{rr}

Replaces January 2000 version, DS4150-6.0

APPLICATIONS

■ Snubber Diode For GTO Applications

KEY PARAMETERS				
V _{RRM}	4500V			
F(AV)	430A			
FSM	3500A			

440μ**C**

3.07µs

DS4146-7.0 June 2004

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- Double side cooling
- High surge capability
- Low recovery charge

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V _{RRM} V	Conditions
DSF8045SK45	4500	$V_{RSM} = V_{RRM} + 100V$
DSF8045SK44	4400	
DSF8045SK43	4300	
DSF8045SK42	4200	
DSF8045SK41	4100	
DSF8045SK40	4000	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table, e.g.:

DSF8045SK43

Note: Please use the complete part number when ordering and quote this number in any future correspondance relating to your order.

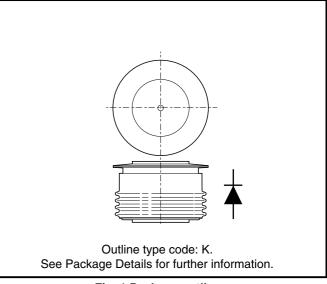


Fig. 1 Package outline



CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units	
Double Sid	e Cooled				
I _{F(AV)}	Mean forward current	Half wave resistive load, T _{case} = 65°C	430	А	
I _{F(RMS)}	RMS value	T _{case} = 65°C	680	А	
I _F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	600	А	
Single Side Cooled (Anode side)					
I _{F(AV)}	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	285	А	
I _{F(RMS)}	RMS value	$T_{case} = 65^{\circ}C$	445	Α	
I _F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	380	А	

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% V _{RBM} T _i = 150°C	3.5	kA
l ² t	I ² t for fusing		61.25 x 10 ³	A²s
I _{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% V _{BRM.} T _i = 150°C	2.8	kA
l ² t	I ² t for fusing		39.2 x 10 ³	A²s

THERMAL AND MECHANICAL DATA

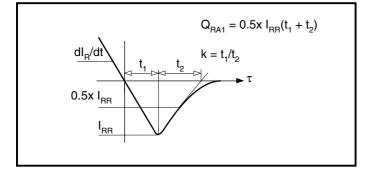
Symbol	Parameter	Conditions		Min.	Max.	Units
		Double side cooled	dc	-	0.048	°C/W
R _{th(j-c)}	R _{th(i-c)} Thermal resistance - junction to case		Anode dc	-	0.09	°C/W
	Single side cooled	Cathode dc	-	0.103	°C/W	
D	R _{th(c-h)} Thermal resistance - case to heatsink	Clamping force 8.0kN with mounting compound	Double side	-	0.01	°C/W
H _{th(c-h)}			Single side	-	0.02	°C/W
T _{vj}	Virtual junction temperature	Forward (conducting)		-	150	°C
T _{stg}	Storage temperature range			-55	175	°C
-	Clamping force			7.0	9.0	kN



CHARACTERISTICS

Symbol	Parameter	Conditions	Тур.	Max.	Units
V _{FM}	Forward voltage	At 1000A peak, T _{case} = 25°C	-	4.0	V
I _{RRM}	Peak reverse current	At V_{RRM} , $T_{\text{case}} = 150^{\circ}\text{C}$	-	50	mA
t _{rr}	Reverse recovery time		-	3.07	μs
Q _{RA1}	Recovered charge (50% chord)	I _F = 1000A, di _{ββ} /dt = 100A/μs	-	440	μC
I _{RM}	Reverse recovery current	$T_{case} = 150^{\circ}C, V_{R} = 100V$	-	240	Α
к	Soft factor		-	-	-
V _{TO}	Threshold voltage	At $T_{vj} = 150^{\circ}C$	-	1.7	v
r _T	Slope resistance	At $T_{vj} = 150^{\circ}C$	-	2.1	mΩ
V _{FRM}	Forward recovery voltage	di/dt = 1000A/µs, T _j = 125°C	-	300	V

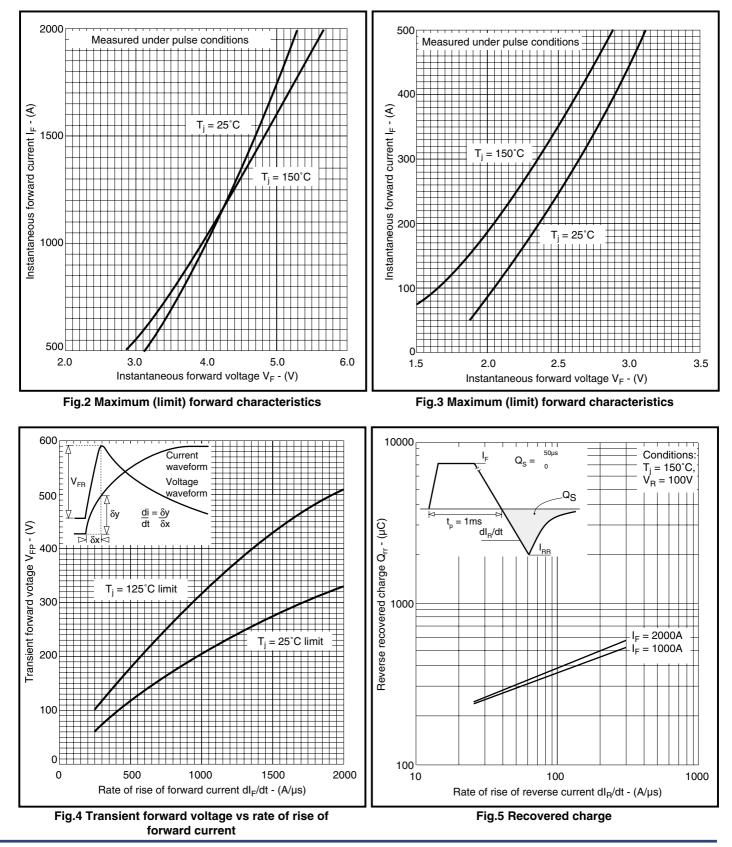
DEFINITION OF K FACTOR AND $\mathbf{Q}_{_{\mathrm{RA1}}}$



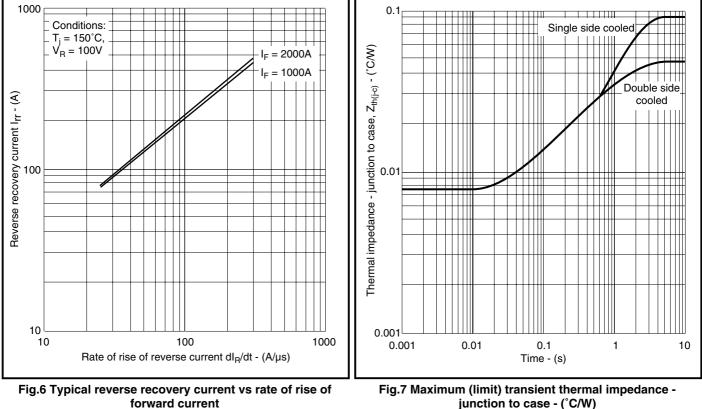
DSF8045SK



CURVES





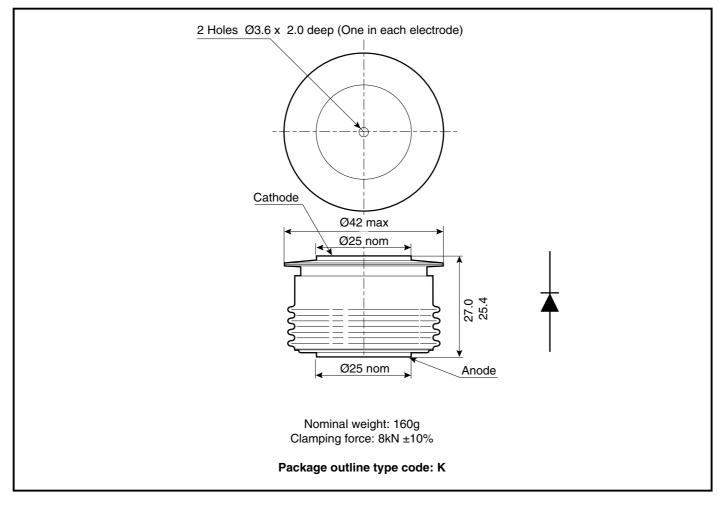


junction to case - (°C/W)



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



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